

SANYO Semiconductors

• 4.0V drive

· Halogen free compliance

DATA SHEET

An ON Semiconductor Company

TIG067SS

N-Channel IGBT **Light-Controlling Flash Applications**

· Built-in Gate-to-Emitter protection diode

Features

- · Low-saturation voltage
- Enhansment type
- · High speed switching

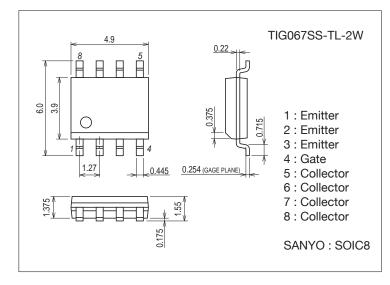
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage (DC)	VCES		400	V
Collector-to-Emitter Voltage (Pulse)	VCESP	PW≤1ms	450	V
Gate-to-Emitter Voltage (DC)	VGES		±6	V
Gate-to-Emitter Voltage (Pulse)	VGESP	PW≤1ms	±8	V
Collector Current (Pulse)	ICP	C _M =600µF	150	А
Maximum Collector-to-Emitter dv / dt	dv / dt	V _{CE} ≤320V, starting Tch=25°C	1500	V/µs
Allowable Power Dissipation	PD	When mounted on FR4 substrate (11,680mm ² ×1.6mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-40 to +150	°C

Package Dimensions

unit : mm (typ) 7072-002



Product & Package Information

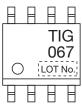
• Package	: SOIC8
• JEITA, JEDEC	: SC-87, SOT-96

• Minimum Packing Quantity : 2500 pcs./reel

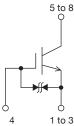
Packing Type: TL

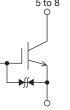
Marking





Electrical Connection





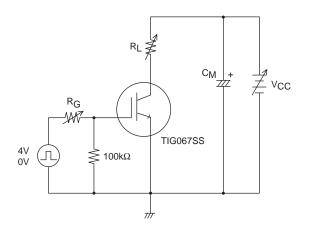


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Electrical Characteristics at Ta=25°C							
Parameter	Symbol	Conditions	Ratings			Unit	
		Conditions	min	typ	max		
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=2mA, VGE=0V	400			V	
Collector-to-Emitter Cutoff Current	ICES	V _{CE} =320V, V _{GE} =0V			10	μA	
Gate-to-Emitter Leakage Current	IGES	V _{GE} =±6V, V _{CE} =0V			±10	μA	
Gate-to-Emitter Threshold Voltage	V _{GE} (off)	V _{CE} =10V, I _C =1mA	0.4		1.0	V	
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=150A, VGE=4V		3.8	5	V	
Input Capacitance	Cies			5100		pF	
Output Capacitance	Coes	V _{CE} =10V, f=1MHz		59		pF	
Reverse Transfer Capacitance	Cres			43		pF	
Fall Time	tf	IC=150A, VCC=320V, Resistor load VGE=4V, RG=36 Ω		270		ns	

Electrical Characteristics at Ta-25°C

Fig1 Large Current R Load Switching Circuit

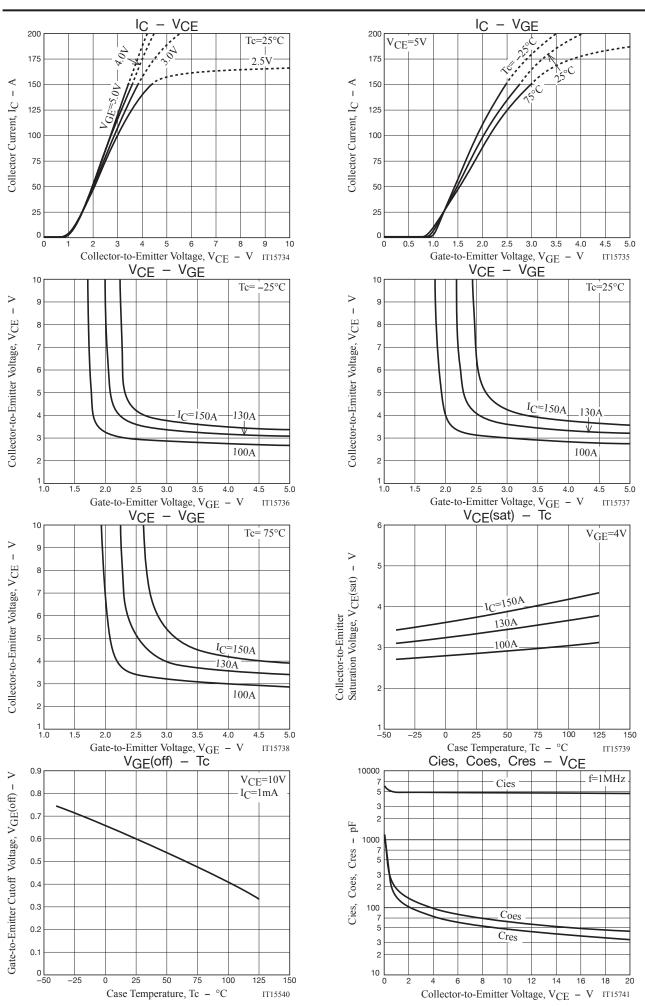


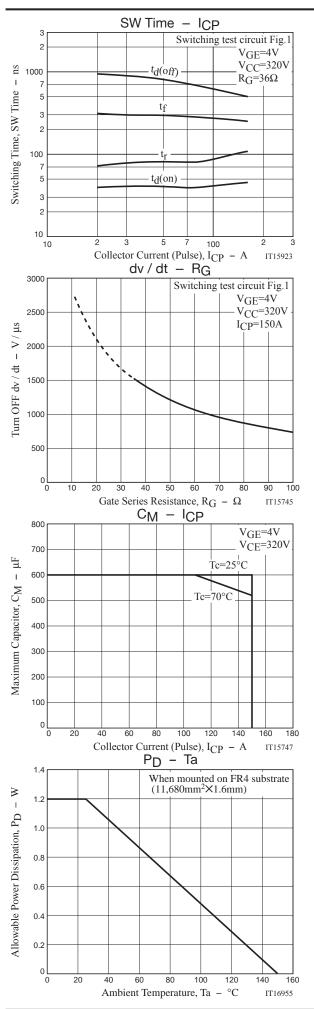
Note1. Gate Series Resistance $R_G \ge 36\Omega$ is recommended for protection purpose at the time of turn OFF. However, if dv / dt \leq 1500 / μ s is satisfied at customer's actual set evaluation, RG < 36 Ω can also be used.

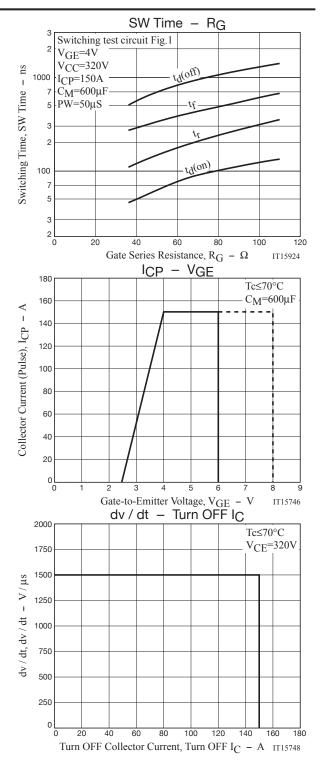
Note2. The collector voltage gradient dv / dt must be smaller than 1500V / μ s to protect the device when it is turned off.

Ordering Information

Device	Package	Shipping	memo	
TIG067SS-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free	





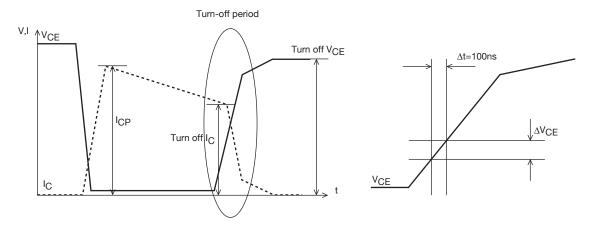


Definition of dv/dt

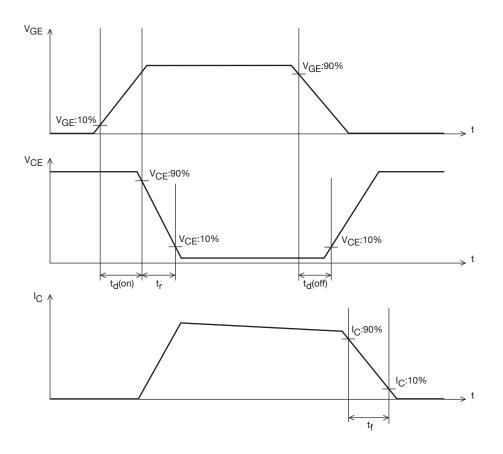
dv/dt is defined as the maximum slope of the below VCE curve during turn-off period. dv/dt= $\Delta VCE/\Delta t=\Delta VCE/100$ ns

Overall waveform

Enlarged picture of turn-off period



Definition of Switching Time



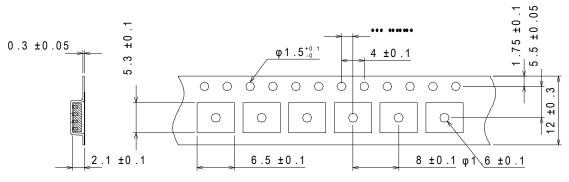
Taping Specification

TIG067SS-TL-2W

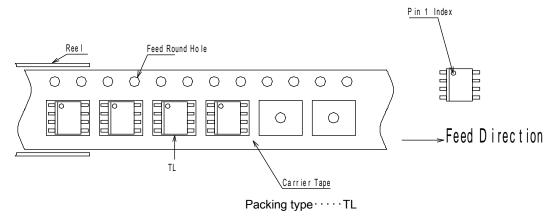
1. Packing Format Packing format Package Name Carrier Tape Maximum Number of devices contained (pcs) Туре Reel Inner box Outer box Inner BOX W206-112 Outer BOX W207-124 SOIC8 B202-101 2,500 12,500 25,000 5 reels contained 2 inner boxes contained Dimensions :mm(external) Dimensions :mm(external) 340×95×340 360×210×375 Packing method Reel label, Inner box label Outer box label (unit: mm) It is a label at the time of factory shipments. The form of a label may change in physical distribution process. 69 108 4 Type No. \rightarrow TYPE COT (P)TYPE 0000000 Λ Λ LOT No. \rightarrow TYPE ര 00000000 43 0,000 pcs Quantity OTY (1)LEAD FREE ※ (0)0T \rightarrow (1)LEAD FREE LOT 00000000 80 Origin \rightarrow Z) SPESIAL OC PACKAGE 00000000 SPECIAL 00000000 SPECIAL NOTE(1) Reel label Z0722005310C The LEAD FREE 4 description shows that ASSEMBLY:****(DIFFUSION:****) it is complete lead free. JEITA Phase Label LEAD FREE 4 JEITA Phase 3

2. Taping configuration

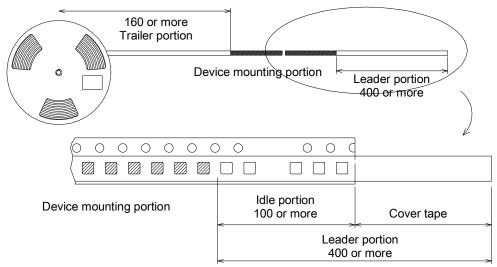
2-1. Carrier tape size (unit: mm)



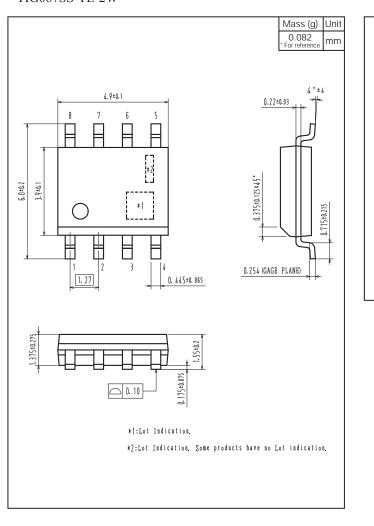
2-2. Device placement direction



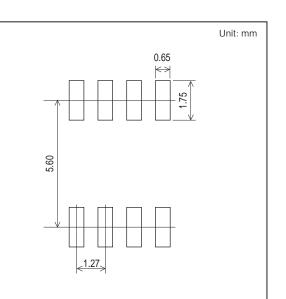
2-3. Leader portion and trailer portion (unit: mm)



Outline Drawing TIG067SS-TL-2W



Land Pattern Example



Note : TIG067SS has protection diode between gate and emitter but handling it requires sufficient care to be taken.

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